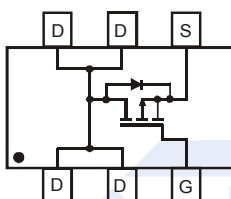
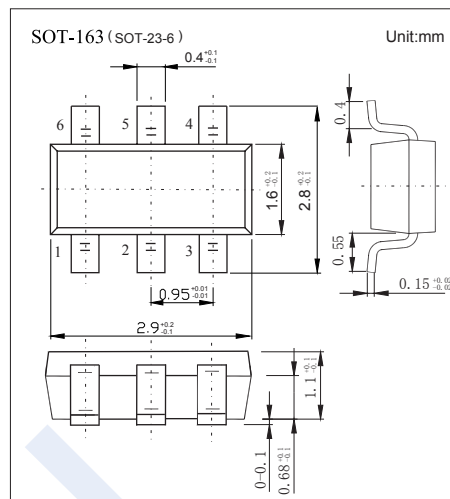


P-Channel MOSFET

DMP2066LDM

■ Features

- $V_{DS}(V) \approx -20V$
- $I_D \approx -4.6 A$
- $R_{DS(ON)} < 40m\Omega$ ($V_{GS} \approx -4.5V$)
- $R_{DS(ON)} < 70m\Omega$ ($V_{GS} \approx -2.5V$)
- Low Input/Output Leakage



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current $T_a = 25^\circ C$ $T_a = 70^\circ C$	I_D	-4.6	A
		-3.7	
Pulsed Drain Current	I_{DM}	-18	
Power Dissipation	P_D	1.25	W
Thermal Resistance Junction- to-Ambient	R_{thJA}	100	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

P-Channel MOSFET

DMP2066LDM

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{BSS}	I _D =-250 μA, V _{GS} =0V	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
Gate-Body leakage current	I _{GSS}	V _{BS} =0V, V _{GS} =±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250 μA	-0.6		-1.2	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-4.6A			40	mΩ
		V _{GS} =-2.5V, I _D =-3.8A			70	
On state drain current	I _{D(ON)}	V _{GS} =-4.5V, V _{DS} =-5V	-15			A
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-4.6A		9		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		820		pF
Output Capacitance	C _{oss}			200		
Reverse Transfer Capacitance	C _{rss}			160		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.5		Ω
Total Gate Charge	Q _g	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-4.5A		10.1		nC
Gate Source Charge	Q _{gs}			1.5		
Gate Drain Charge	Q _{gd}			4.3		
Turn-On DelayTime	t _{d(on)}	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -1A, R _G = 6Ω		4.4		ns
Turn-On Rise Time	t _r			9.9		
Turn-Off DelayTime	t _{d(off)}			28		
Turn-Off Fall Time	t _f			23.4		
Maximum Body-Diode Continuous Current	I _S				-1.7	A
Diode Forward Voltage	V _{SD}	I _S =-2.1A, V _{GS} =0V	-0.5		-1.4	V

■ Marking

Marking	DMC**
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P-Channel MOSFET

DMP2066LDM

■ Typical Characteristics

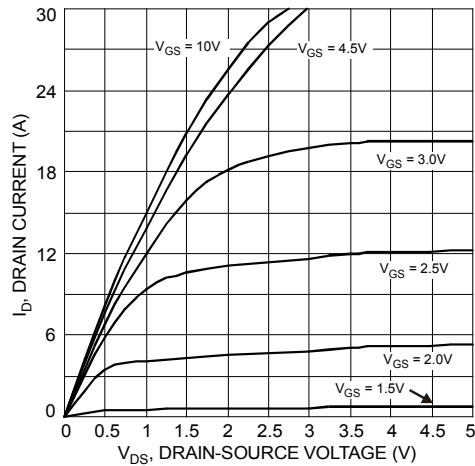


Fig. 1 Typical Output Characteristic

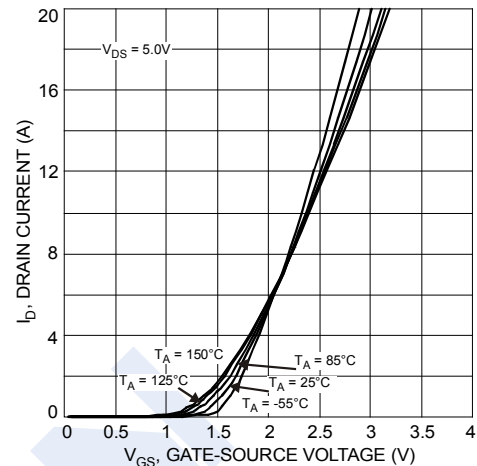


Fig. 2 Typical Transfer Characteristic

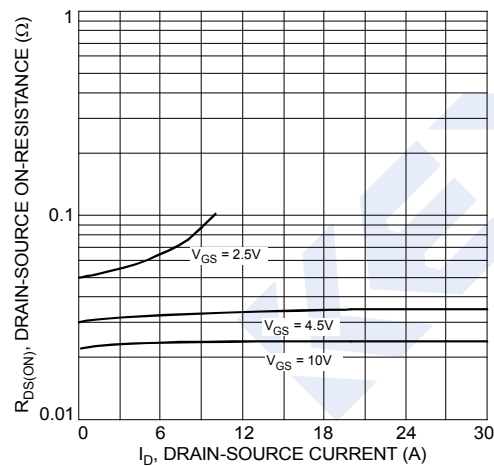


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

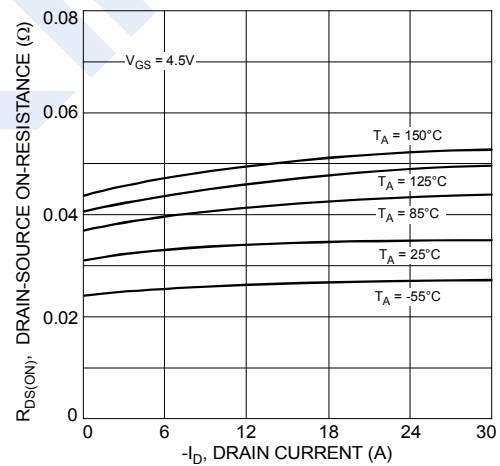


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

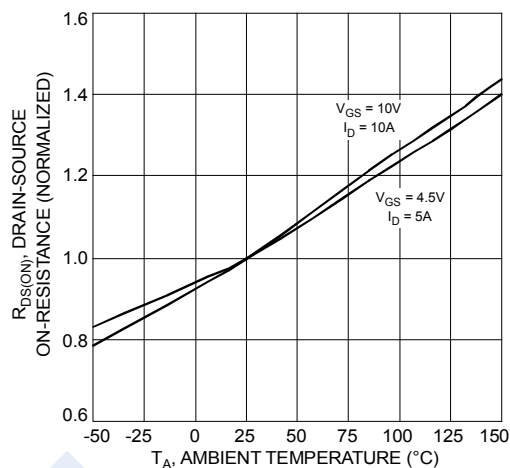


Fig. 5 Normalized On-Resistance vs. Ambient Temperature

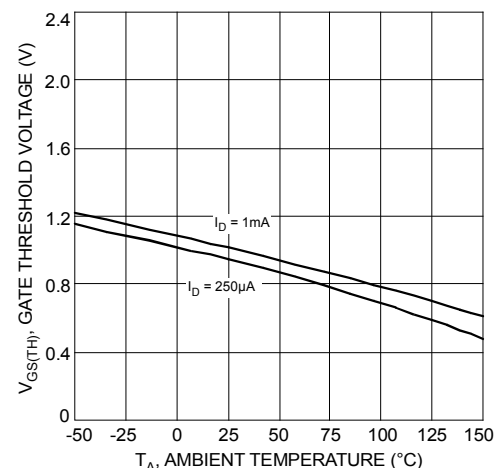


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

P-Channel MOSFET

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■ Typical Characteristics

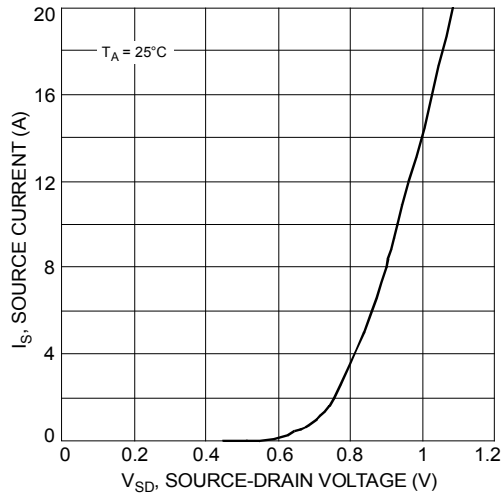


Fig. 7 Diode Forward Voltage vs. Current

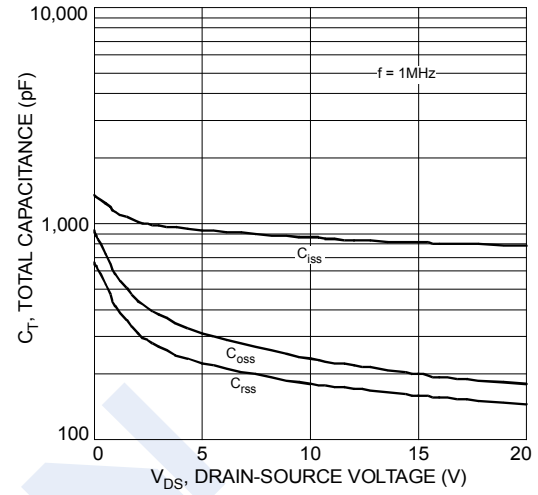


Fig. 8 Typical Total Capacitance

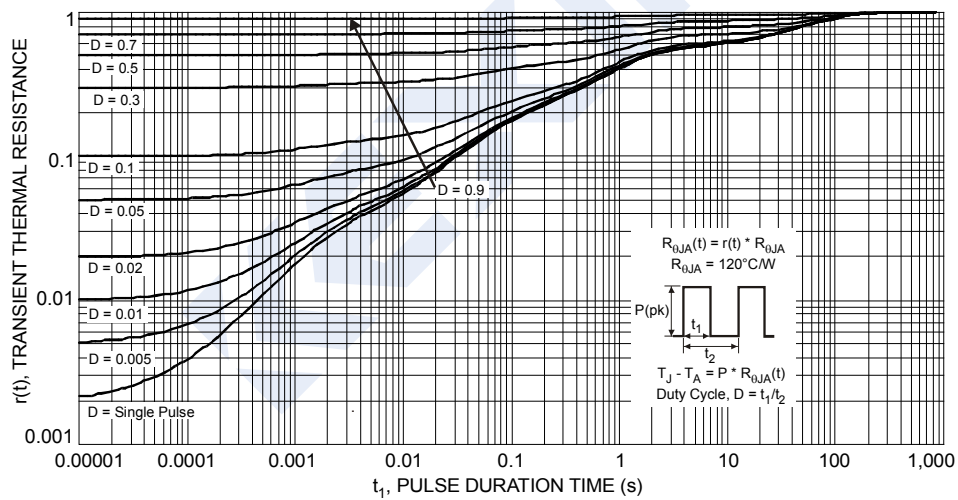


Fig. 9 Transient Thermal Response